LME49721 High Performance, High Fidelity Rail-to-Rail Input/Output Audio Operational Amplifier

Check for Samples: LME49721

FEATURES

- **Rail-to-rail Input and Output**
- **Easily drives 10kΩ loads to within 10mV of each power supply voltage**
- **Optimized for superior audio signal fidelity**
- **Output short circuit protection**

APPLICATIONS

- **Ultra high quality portable audio amplification**
- **High fidelity preamplifiers**
- **High fidelity multimedia**
- **State of the art phono pre amps**
- **High performance professional audio**
- **High fidelity equalization and crossover networks**
- **High performance line drivers**
- **High performance line receivers**
- **High fidelity active filters**
- **DAC I–V converter**
- **ADC front-end signal conditioning**

DESCRIPTION

The LME49721 is a low distortion, low noise Rail-to-Rail Input/Output operational amplifier optimized and fully specified for high performance, high fidelity applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LME49721 Rail-to-Rail Input/Output operational amplifier delivers superior signal amplification for outstanding performance. The LME49721 combines a very high slew rate with low THD+N to easily satisfy demanding applications. To ensure that the most challenging loads are driven without compromise, the LME49721 has a high slew rate of ±8.5V/μs and an output current capability of ±9.7mA. Further, dynamic range is maximized by an output stage that drives 10kΩ loads to within 10mV of either power supply voltage.

The LME49721 has a wide supply range of 2.2V to 5.5V. Over this supply range the LME49721's input circuitry maintains excellent common-mode and power supply rejection, as well as maintaining its low input bias current. The LME49721 is unity gain stable.

Table 1. Key Specifications

	VALUE	UNIT
Power Supply Voltage Range	2.2V to 5.5	V
Quiescent Current	2.15	mA (typ)
THD+N (A_V = 2, V_{OUT} = $4V_{p-p}$, f_{IN} = 1kHz) R_L = 2kΩ R_L = 600Ω	 0.00008 0.0001	% (typ)
Input Noise Density	4nV/√Hz (typ), @ 1	kHz
Slew Rate	±8.5V/μs (typ)	
Gain Bandwidth Product	20	MHz (typ)
Open Loop Gain (R_L = 600Ω)	118	dB (typ)
Input Bias Current	40	fA (typ)
Input Offset Voltage	0.3mV (typ)	
PSRR	103	dB (typ)

Typical Connection, Pinout, and Package Marking

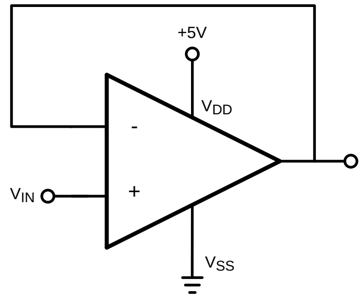


Figure 1. Buffer Amplifier

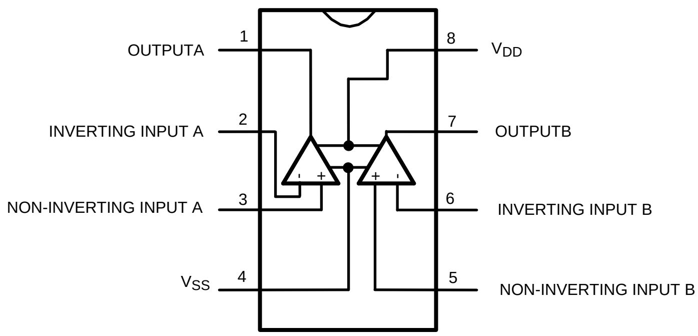
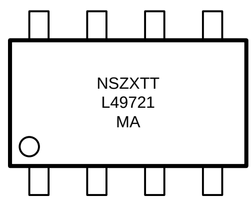


Figure 2.



NS = National Logo, Z = Assembly plant code, X = 1 Digit date code, TT = Lot traceability, L49721 = LME49721, MA = Narrow SOIC package code

Figure 3. Package Marking

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings (1) (2)

Power Supply Voltage ($V_S = V^+ - V^-$)	6V
Storage Temperature	−65°C to 150°C
Input Voltage	(V-) - 0.7V to (V+) + 0.7V
Output Short Circuit (Note 3)	Continuous
Power Dissipation	Internally Limited
ESD Rating (Note 4)	2000V
ESD Rating (Note 5)	200V
Junction Temperature	150°C
Thermal Resistance, θ_{JA} (SO)	165°C/W
Temperature Range, $T_{MIN} \leq T_A \leq T_{MAX}$	–40°C ≤ T_A ≤ 85°C
Supply Voltage Range	2.2V ≤ V_S ≤ 5.5V

(1) "*Absolute Maximum Ratings*" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the *Absolute Maximum Ratings* or other conditions beyond those indicated in the Recommended Operating Conditions is not implied. The *Recommended Operating Conditions* indicate conditions at which the device is functional and the device should not be operated beyond such conditions. All voltages are measured with respect to the ground pin, unless otherwise specified

(2) The *Electrical Characteristics* tables list guaranteed specifications under the listed *Recommended Operating Conditions* except as otherwise modified or specified by the *Electrical Characteristics Conditions* and/or Notes. Typical specifications are estimations only and are not guaranteed.

Electrical Characteristics for the LME49721

The following specifications apply for the circuit shown in Figure 4. V_S = 5V, R_L = 10kΩ, R_{SOURCE} = 10Ω, f_{IN} = 1kHz, and T_A = 25°C, unless otherwise specified.

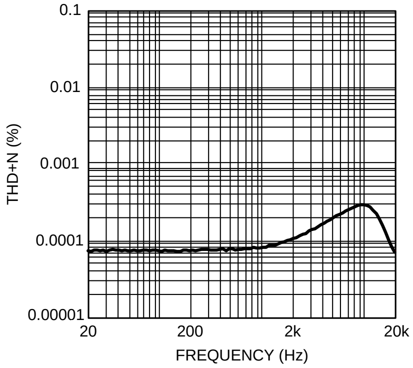
Symbol	Parameter	Conditions	LME49721 Typical (1)	LME49721 Limit (2)	Units (Limits)
THD+N	Total Harmonic Distortion + Noise	A_V = +1, V_{OUT} = $2V_{p-p}$, R_L = 2kΩ R_L = 600Ω	 0.0002 0.0002	 0.001	 % (max)
IMD	Intermodulation Distortion	A_V = +1, V_{OUT} = $2V_{p-p}$, Two-tone, 60Hz & 7kHz 4:1	0.0004		%
GBWP	Gain Bandwidth Product		20	15	MHz (min)
SR	Slew Rate	A_V = +1	8.5		V/μs (min)
FPBW	Full Power Bandwidth	V_{OUT} = $1V_{P-P}$, –3dB referenced to output magnitude at f = 1kHz	2.2		MHz
t_s	Settling time	A_V = 1, 4V step 0.1% error range	800		ns
e_n	Equivalent Input Noise Voltage	f_{BW} = 20Hz to 20kHz, A-weighted	.707	1.13	μV_{P-P} (max)
	Equivalent Input Noise Density	f = 1kHz A-weighted	4	6	nV/√Hz (max)
I_n	Current Noise Density	f = 10kHz	4.0		fA/√Hz
V_{OS}	Offset Voltage		0.3	1.5	mV (max)
$\Delta V_{OS}/\Delta$Temp	Average Input Offset Voltage Drift vs Temperature	40°C ≤ T_A ≤ 85°C	1.1		μV/°C
PSRR	Average Input Offset Voltage Shift vs Power Supply Voltage		103	85	dB (min)
ISO_{CH-CH}	Channel-to-Channel Isolation	f_{IN} = 1kHz	117		dB
I_B	Input Bias Current	V_{CM} = V_S/2	40		fA
$\Delta I_{OS}/\Delta$Temp	Input Bias Current Drift vs Temperature	–40°C ≤ T_A ≤ 85°C	48		fA/°C
I_{OS}	Input Offset Current	V_{CM} = V_S/2	60		fA
V_{IN-CM}	Common-Mode Input Voltage Range			(V+) – 0.1 (V-) + 0.1	V (min)
CMRR	Common-Mode Rejection	V_{SS} - 100mV < V_{CM} < V_{DD} + 100mV	93	70	dB (min)
	1/f Corner Frequency		2000		Hz
A_{VOL}	Open Loop Voltage Gain	V_{SS} - 200mV < V_{OUT} < V_{DD} + 200mV			
		R_L = 600Ω	118	100	dB (min)
		R_L = 2kΩ	122		dB (min)
		R_L = 10kΩ	130	115	dB (min)
V_{OUTMIN}	Output Voltage Swing	R_L = 600Ω	V_{DD} – 30mV	V_{DD} – 80mV	V (min)
			V_{SS} + 30mV	V_{SS} + 80mV	V (min)
		R_L = 10kΩ, V_S = 5.0V	V_{DD} – 10mV	V_{DD} – 20mV	V (min)
			V_{SS} + 10mV	V_{SS} + 20mV	V (min)
I_{OUT}	Output Current	R_L = 250Ω, V_S = 5.0V	9.7	9.3	mA (min)
I_{OUT-SC}	Short Circuit Current		100		mA
R_{OUT}	Output Impedance	f_{IN} = 10kHz Closed-Loop Open-Loop	 0.01 46		Ω
I_S	Quiescent Current per Amplifier	I_{OUT} = 0mA	2.15	3.25	mA (max)

(1) Typical values represent most likely parametric norms at T_A = +25ºC, and at the *Recommended Operation Conditions* at the time of product characterization and are not guaranteed.
(2) Datasheet min/max specification limits are guaranteed by test or statistical analysis.

Typical Performance Characteristics

Graphs were taken in dual supply configuration.

THD+N vs Frequency
V_S = ±2.5V, V_{OUT} = $4V_{P-P}$
R_L = 2kΩ, A_V = 2, BW = 22kHz



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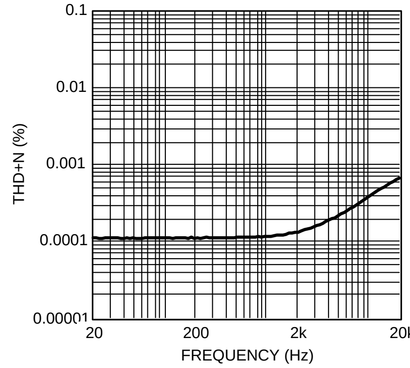
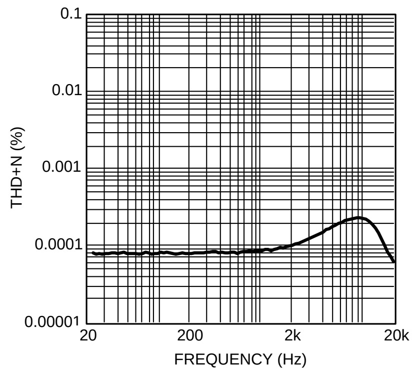


THD+N vs Frequency
V_S = ±2.5V, V_{OUT} = $4V_{P-P}$
R_L = 10kΩ, A_V = 2, BW = 22kHz



THD+N vs Frequency
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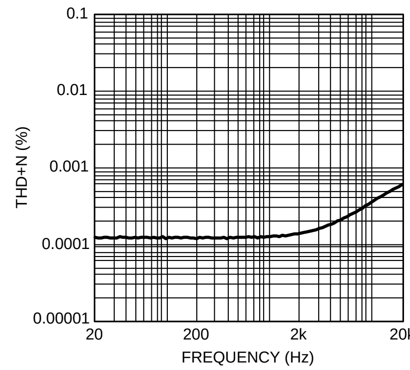
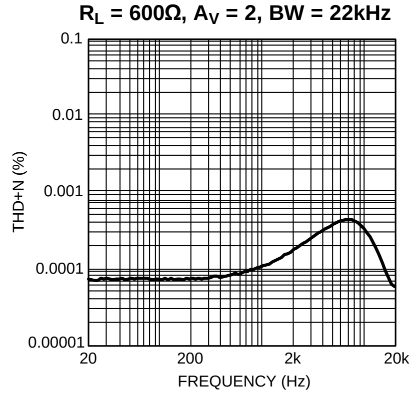
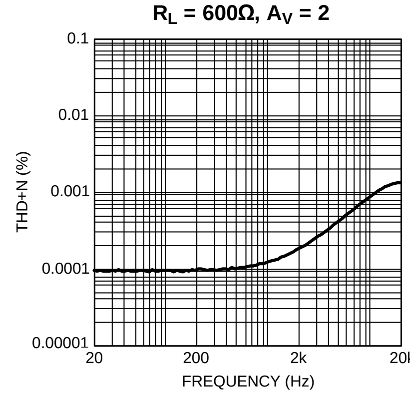
R_L = 10kΩ, A_V = 2



THD+N vs Frequency
V_S = ±2.5V, V_{OUT} = $4V_{P-P}$
R_L = 600Ω, A_V = 2, BW = 22kHz



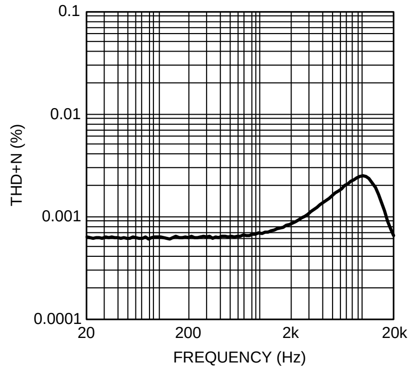
THD+N vs Frequency
V_S = ±2.5V, V_{OUT} = $4V_{P-P}$
R_L = 600Ω, A_V = 2



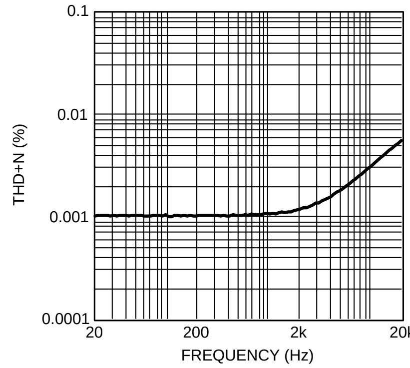
Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

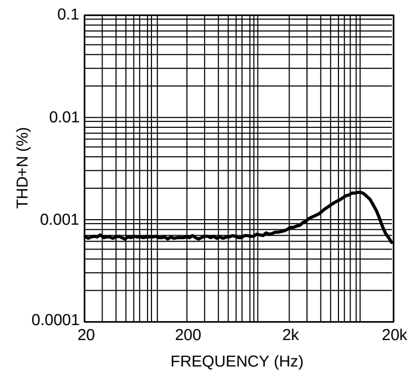
THD+N vs Frequency
V_S = ±2.75V, V_{OUT} = 4V_{P-P}
R_L = 2kΩ, A_V = 2, BW = 22kHz



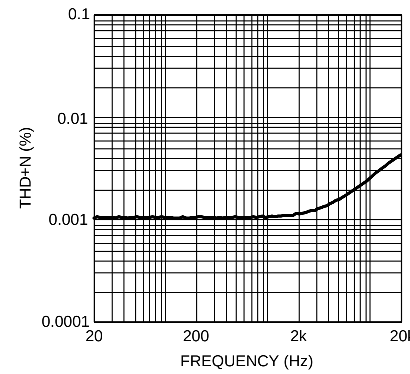
THD+N vs Frequency
V_S = ±2.75V, V_{OUT} = 4V_{P-P}
R_L = 2kΩ, A_V = 2



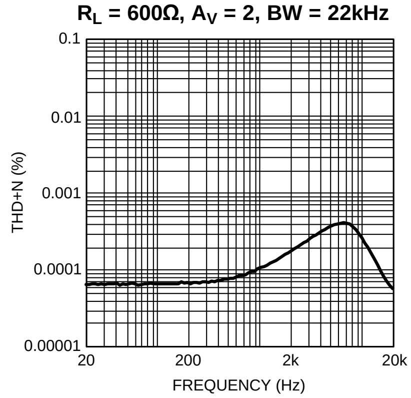
THD+N vs Frequency
V_S = ±2.75V, V_{OUT} = 4V_{P-P}
R_L = 10kΩ, A_V = 2, BW = 22kHz



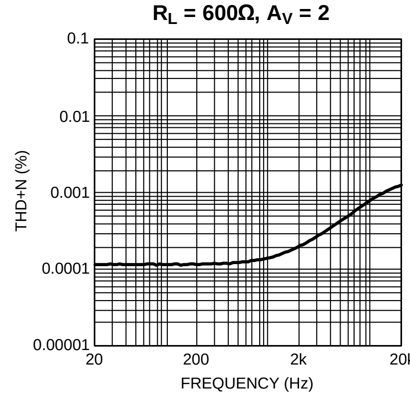
THD+N vs Frequency
V_S = ±2.75V, V_{OUT} = 4V_{P-P}
R_L = 10kΩ, A_V = 2



THD+N vs Frequency
V_S = ±2.75V, V_{OUT} = 4V_{P-P}
R_L = 600Ω, A_V = 2, BW = 22kHz



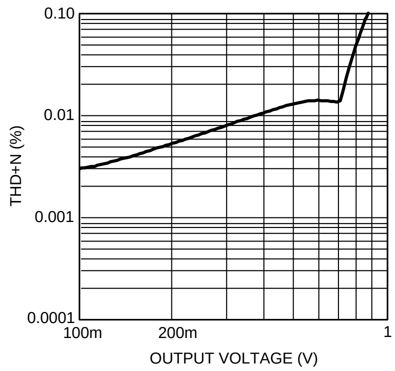
THD+N vs Frequency
V_S = ±2.75V, V_{OUT} = 4V_{P-P}
R_L = 600Ω, A_V = 2



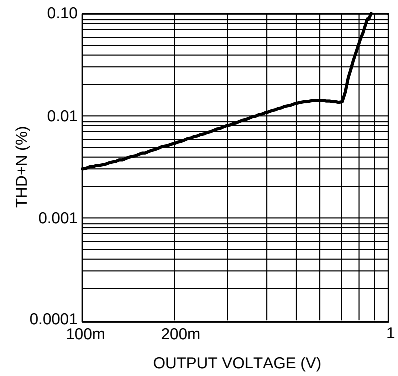
Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

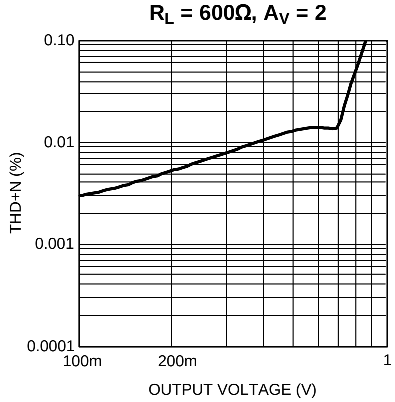
THD+N vs Output Voltage $V_S = \pm1.1V$ $R_L = 2k\Omega, A_V = 2$



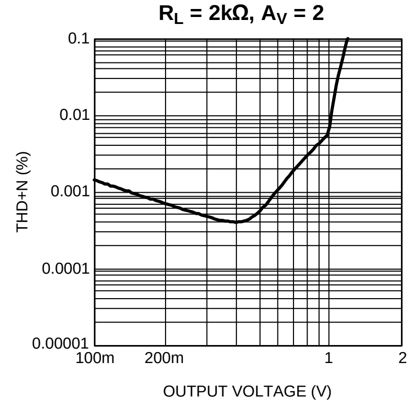
THD+N vs Output Voltage $V_S = \pm1.1V$ $R_L = 10k\Omega, A_V = 2$



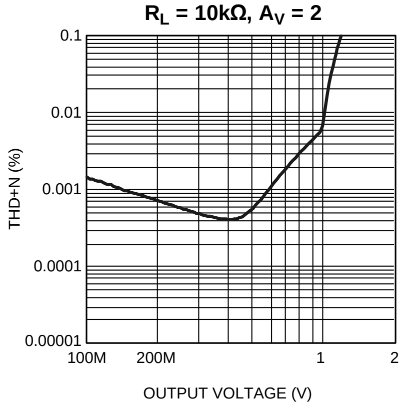
THD+N vs Output Voltage $V_S = \pm1.1V$ $R_L = 600\Omega, A_V = 2$



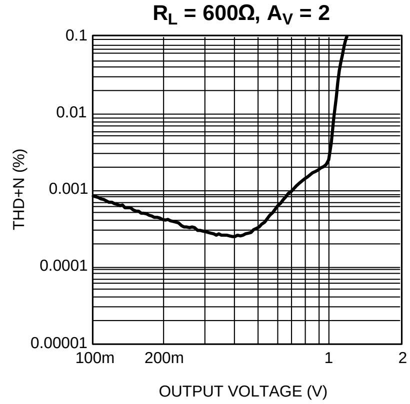
THD+N vs Output Voltage $V_S = \pm1.5V$ $R_L = 2k\Omega, A_V = 2$



THD+N vs Output Voltage $V_S = \pm1.5V$ $R_L = 10k\Omega, A_V = 2$



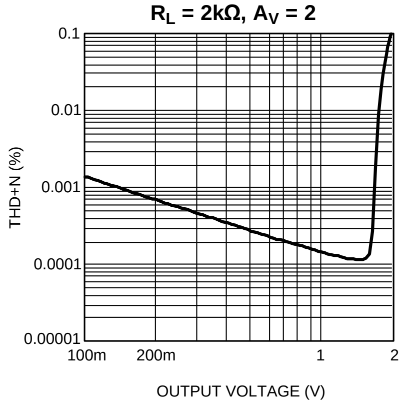
THD+N vs Output Voltage $V_S = \pm1.5V$ $R_L = 600\Omega, A_V = 2$



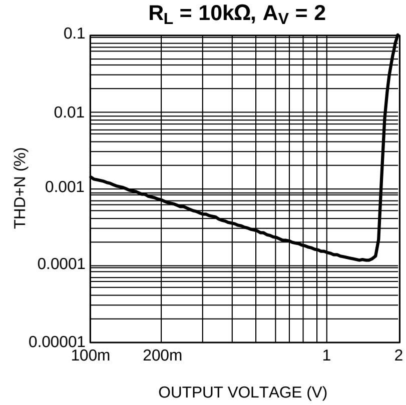
Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

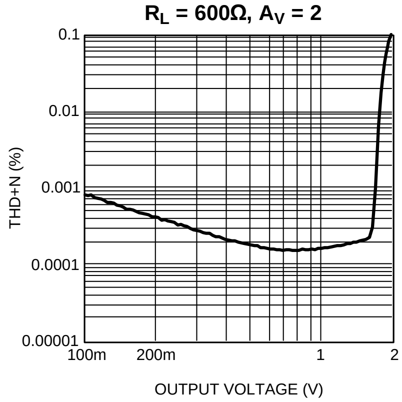
THD+N vs Output Voltage $V_S = \pm 2.5V$ $R_L = 2k\Omega, A_V = 2$



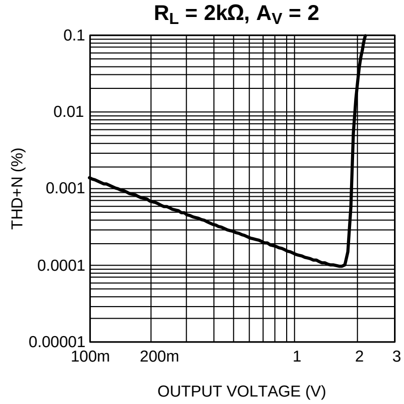
THD+N vs Output Voltage $V_S = \pm 2.5V$ $R_L = 10k\Omega, A_V = 2$



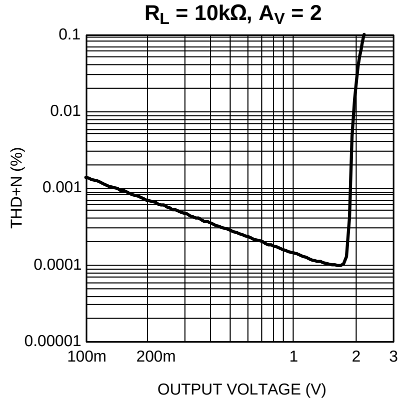
THD+N vs Output Voltage $V_S = \pm 2.5V$ $R_L = 600\Omega, A_V = 2$



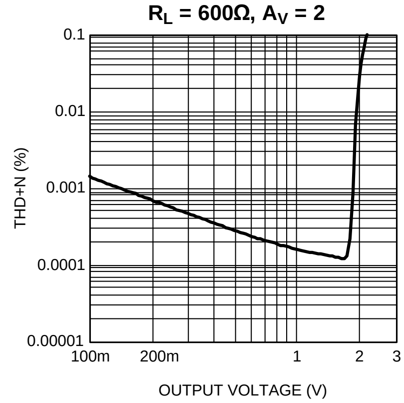
THD+N vs Output Voltage $V_S = \pm 2.75V$ $R_L = 2k\Omega, A_V = 2$



THD+N vs Output Voltage $V_S = \pm 2.75V$ $R_L = 10k\Omega, A_V = 2$



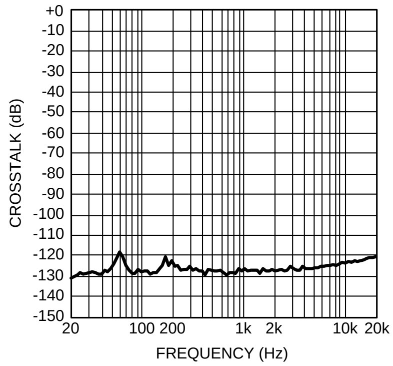
THD+N vs Output Voltage $V_S = \pm 2.75V$ $R_L = 600\Omega, A_V = 2$



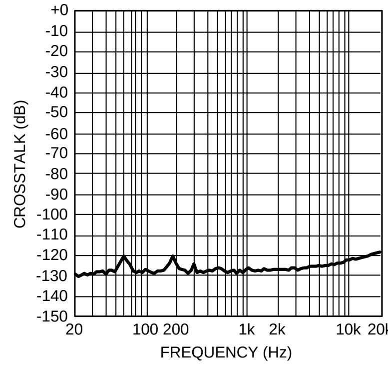
Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

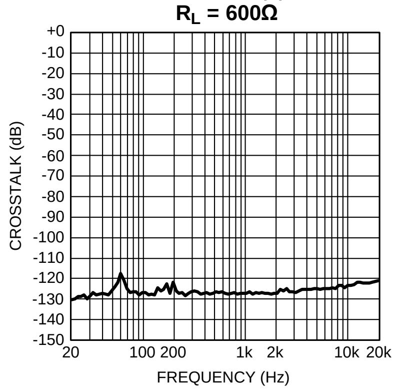
Crosstalk vs Frequency $V_S = \pm1.1V$ $V_{OUT} = 2V_{p-p}$ $R_L = 2k\Omega$



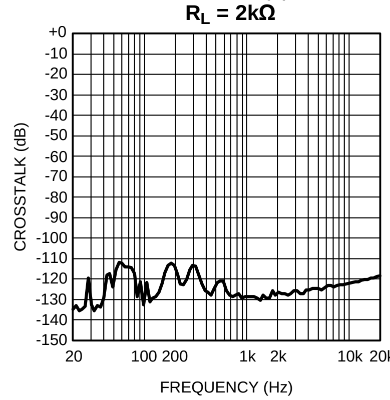
Crosstalk vs Frequency $V_S = \pm1.1V$ $V_{OUT} = 2V_{p-p}$ $R_L = 10k\Omega$



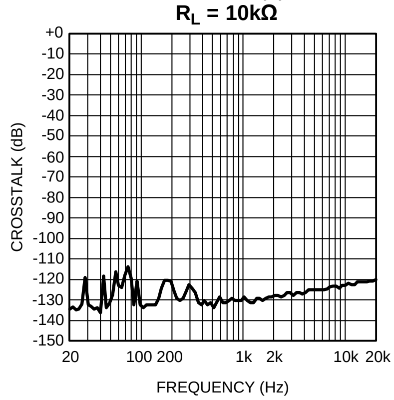
Crosstalk vs Frequency $V_S = \pm1.1V$ $V_{OUT} = 2V_{p-p}$ $R_L = 600\Omega$



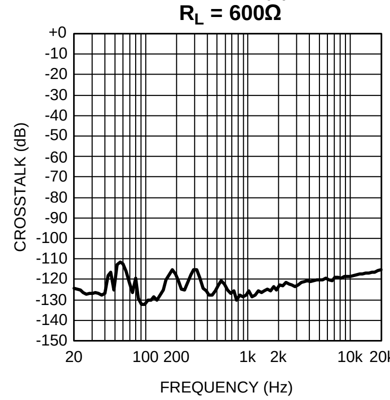
Crosstalk vs Frequency $V_S = \pm1.5V$, $V_{OUT} = 2V_{p-p}$ $R_L = 2k\Omega$



Crosstalk vs Frequency $V_S = \pm1.5V$ $V_{OUT} = 2V_{p-p}$ $R_L = 10k\Omega$



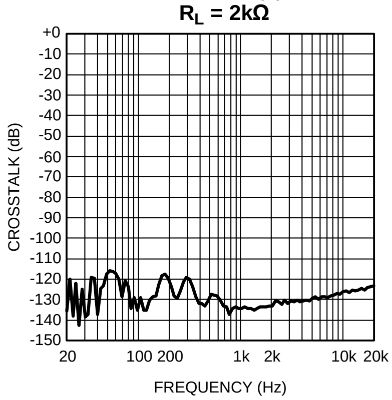
Crosstalk vs Frequency $V_S = \pm1.5V$ $V_{OUT} = 2V_{p-p}$ $R_L = 600\Omega$



Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

Crosstalk vs Frequency
$V_S = \pm2.5V$
$V_{OUT} = 4V_{p-p}$
$R_L = 2k\Omega$



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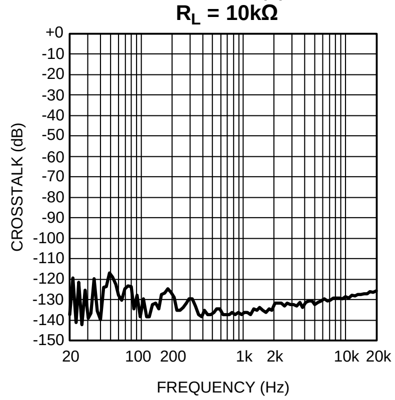

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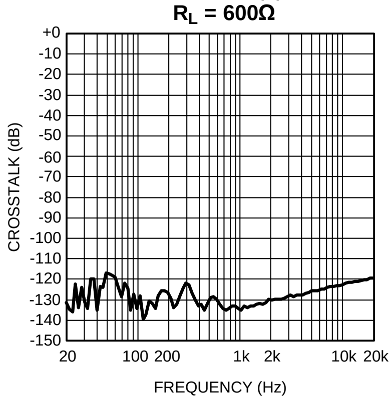
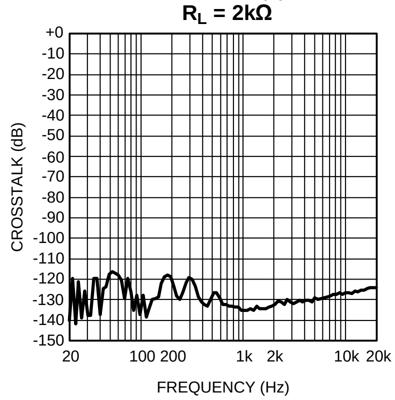


Crosstalk vs Frequency
$V_S = \pm2.75V$
$V_{OUT} = 4V_{p-p}$
$R_L = 2k\Omega$



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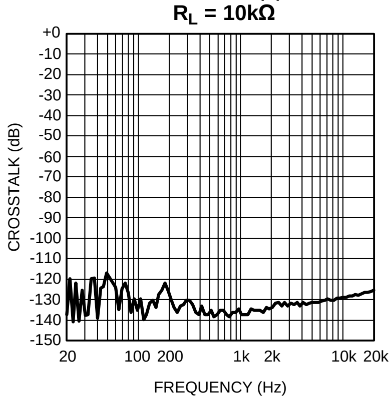

Crosstalk vs Frequency
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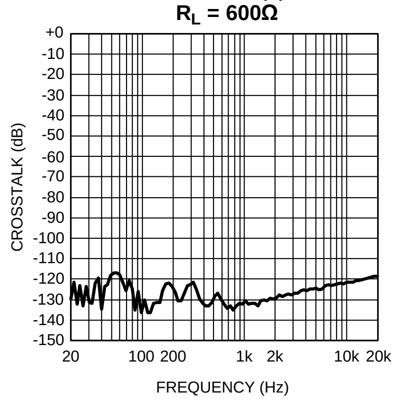
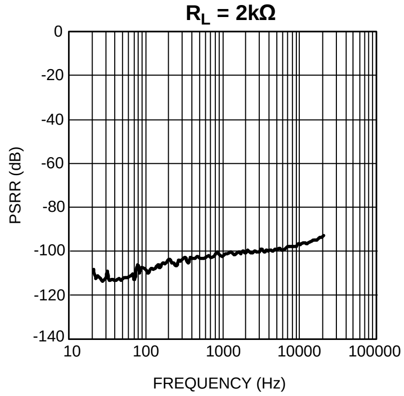


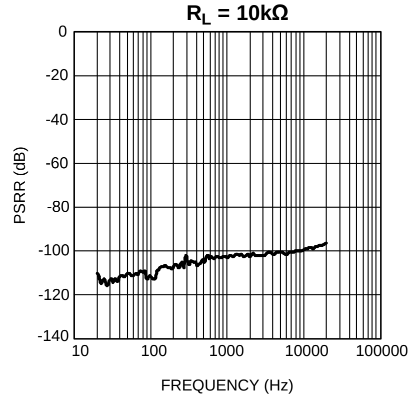
Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

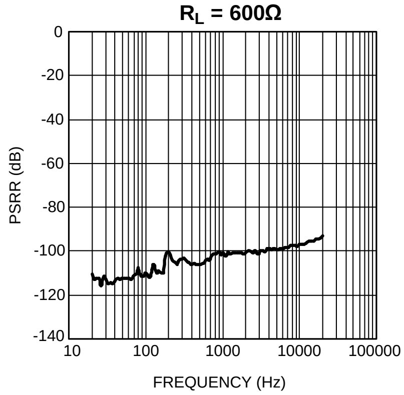
PSRR vs Frequency
V_S = ±1.1V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 2kΩ



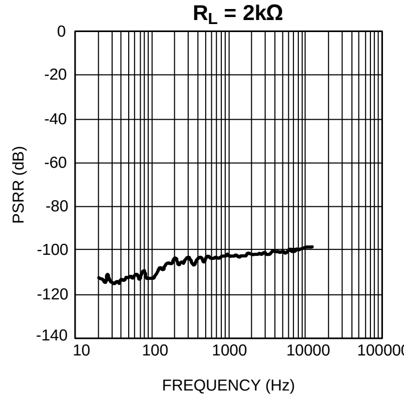
PSRR vs Frequency
V_S = ±1.1V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 10kΩ



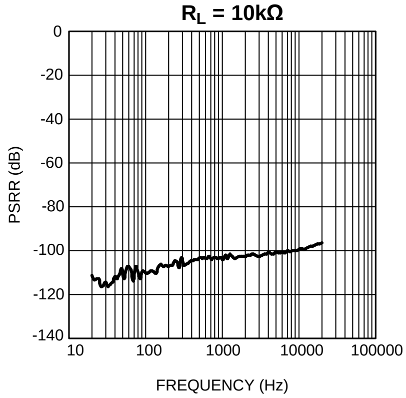
PSRR vs Frequency
V_S = ±1.1V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 600Ω



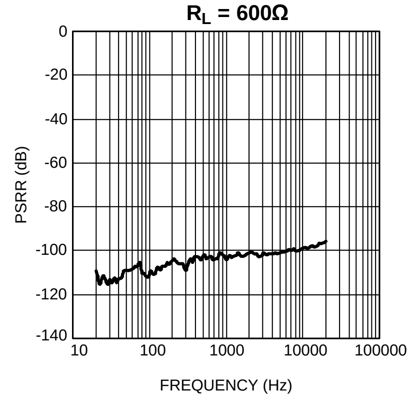
PSRR vs Frequency
V_S = ±1.5V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 2kΩ



PSRR vs Frequency
V_S = ±1.5V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 10kΩ



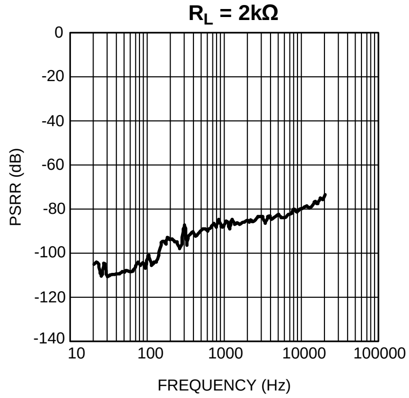
PSRR vs Frequency
V_S = ±1.5V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 600Ω



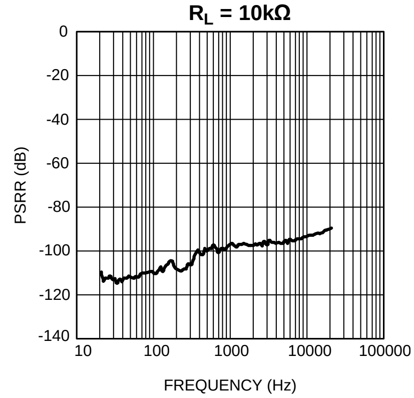
Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

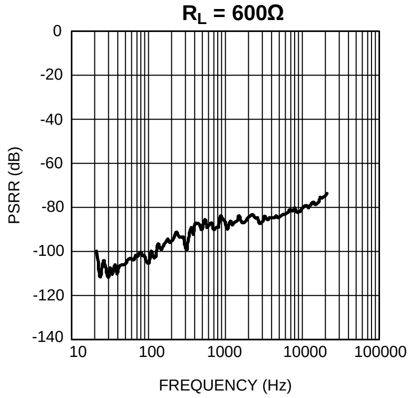
PSRR vs Frequency
V_S = ±2.5V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 2kΩ



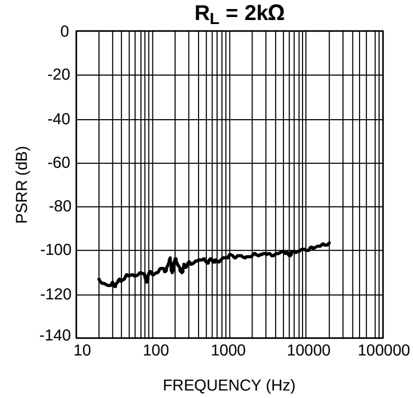
PSRR vs Frequency
V_S = ±2.5V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 10kΩ



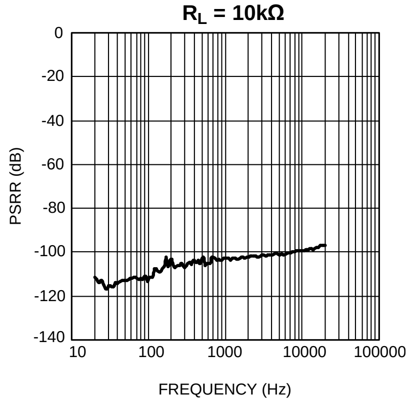
PSRR vs Frequency
V_S = ±2.5V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 600Ω



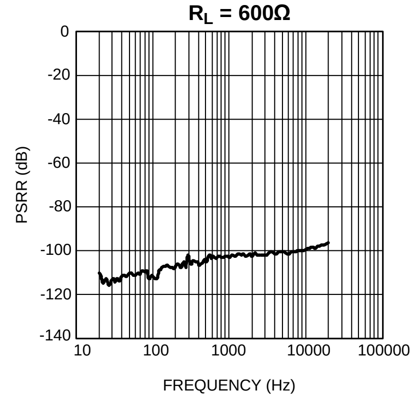
PSRR vs Frequency
V_S = ±2.75V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 2kΩ



PSRR vs Frequency
V_S = ±2.75V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 10kΩ



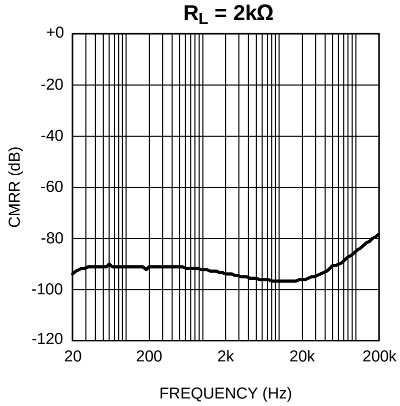
PSRR vs Frequency
V_S = ±2.75V
V_{RIPPLE} = 200mV$_{P-P}$
R_L = 600Ω



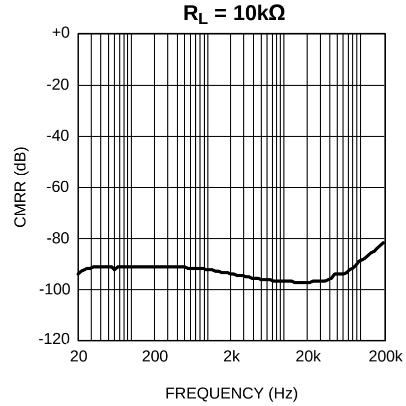
Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

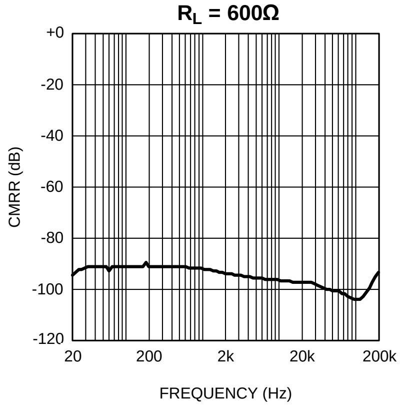
CMRR vs Frequency $V_S = \pm 1.5V$ $R_L = 2k\Omega$



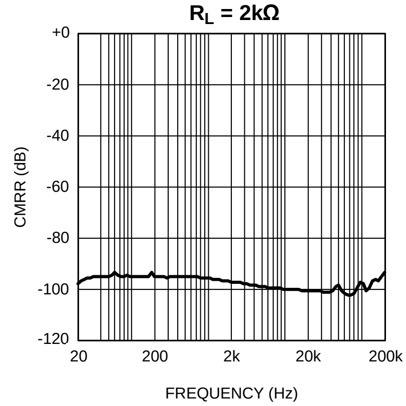
CMRR vs Frequency $V_S = \pm 1.5V$ $R_L = 10k\Omega$



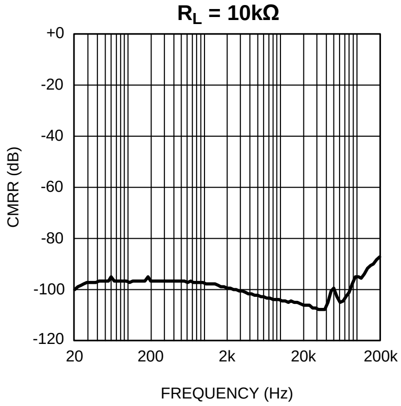
CMRR vs Frequency $V_S = \pm 1.5V$ $R_L = 600\Omega$



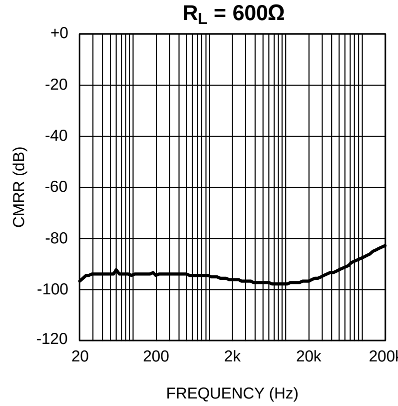
CMRR vs Frequency $V_S = \pm 2.5V$ $R_L = 2k\Omega$



CMRR vs Frequency $V_S = \pm 2.5V$ $R_L = 10k\Omega$



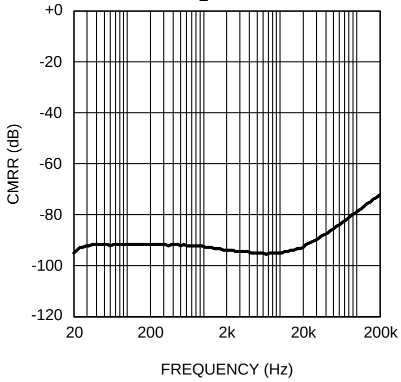
CMRR vs Frequency $V_S = \pm 2.5V$ $R_L = 600\Omega$



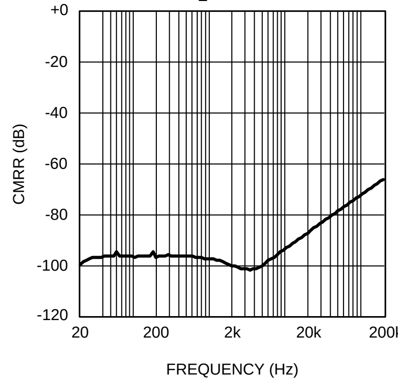
Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

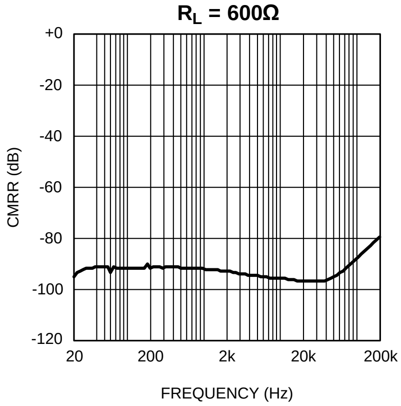
CMRR vs Frequency V_S = ±2.75V R_L = 2kΩ



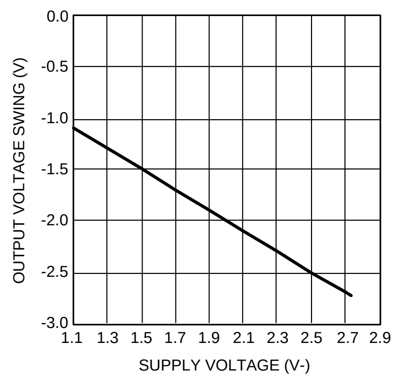
CMRR vs Frequency V_S = ±2.75V R_L = 10kΩ



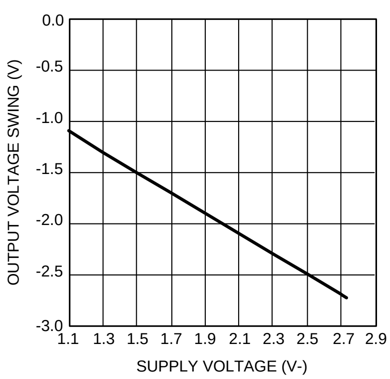
CMRR vs Frequency V_S = ±2.75V R_L = 600Ω



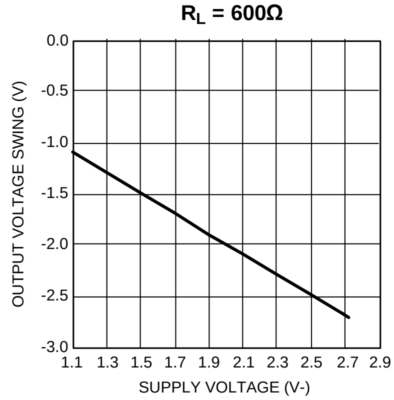
Output Voltage Swing Neg vs Power Supply R_L = 2kΩ



Output Voltage Swing Neg vs Power Supply R_L = 10kΩ



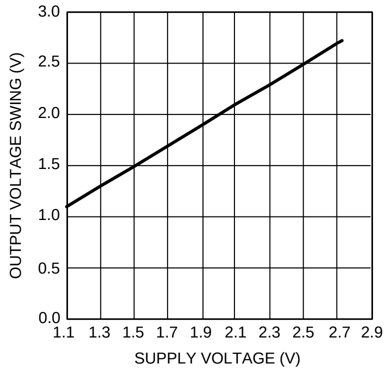
Output Voltage Swing Neg vs Power Supply R_L = 600Ω



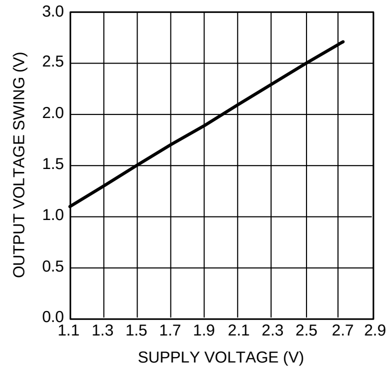
Typical Performance Characteristics (continued)

Graphs were taken in dual supply configuration.

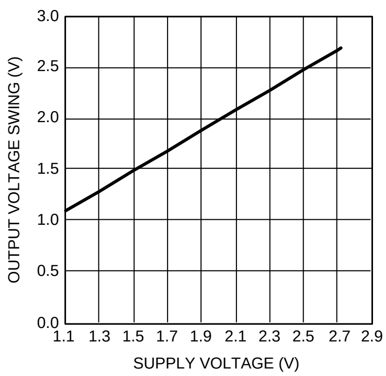
Output Voltage Swing Pos vs Power Supply R_L = 2kΩ



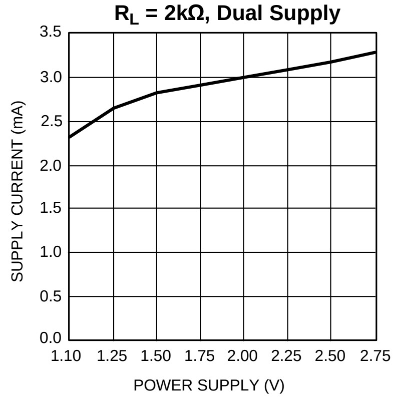
Output Voltage Swing Pos vs Power Supply R_L = 10kΩ



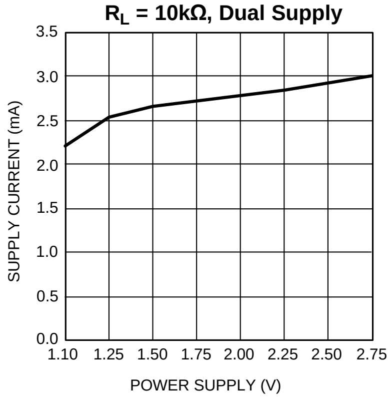
Output Voltage Swing Pos vs Power Supply R_L = 600Ω



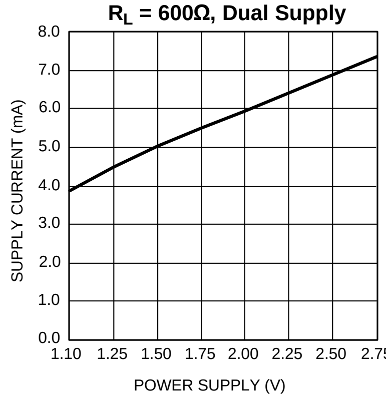
Supply Current per amplifier vs Power Supply R_L = 2kΩ, Dual Supply



Supply Current per amplifier vs Power Supply R_L = 10kΩ, Dual Supply



Supply Current per amplifier vs Power Supply R_L = 600Ω, Dual Supply



Application Information

DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LME49721 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution. however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49721's low residual is an input referred internal error. As shown in Figure 4, adding the 10Ω resistor connected between a the amplifier's inverting and non-inverting inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 4.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so, produces distortion components that are within equipments capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.

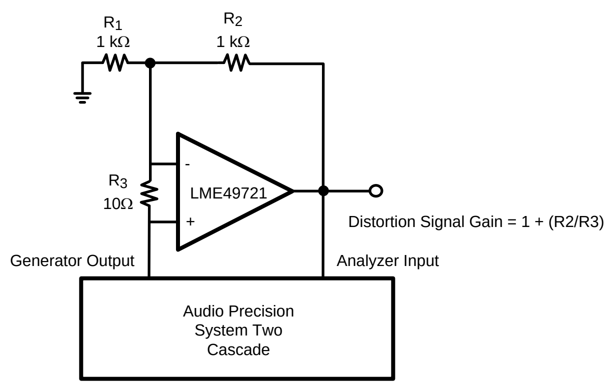


Figure 4. THD+N and IMD Distortion Test Circuit with A_V = 2

OPERATING RATINGS AND BASIC DESIGN GUIDELINES

The LME49721 has a supply voltage range from +2.2V to +5.5V single supply or ±1.1 to ±2.75V dual supply.

Bypassed capacitors for the supplies should be placed as close to the amplifier as possible. This will help minimize any inductance between the power supply and the supply pins. In addition to a 10μF capacitor, a 0.1μF capacitor is also recommended in CMOS amplifiers.

The amplifier's inputs lead lengths should also be as short as possible. If the op amp does not have a bypass capacitor, it may oscillate.

BASIC AMPLIFIER CONFIGURATIONS

The LME49721 may be operated with either a single supply or dual supplies. Figure 5 shows the typical connection for a single supply inverting amplifier. The output voltage for a single supply amplifier will be centered around the common-mode voltage Vcm. Note, the voltage applied to the Vcm insures the output stays above ground. Typically, the Vcm should be equal to V_{DD}/2. This is done by putting a resistor divider ckt at this node, see Figure 5.

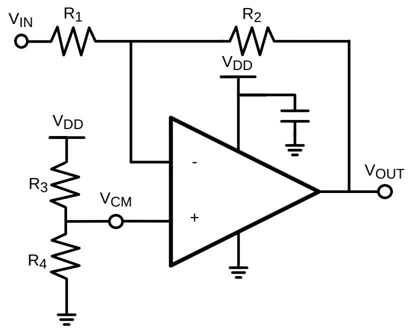


Figure 5. Single Supply Inverting Op Amp

Figure 6 shows the typical connection for a dual supply inverting amplifier. The output voltage is centered on zero.

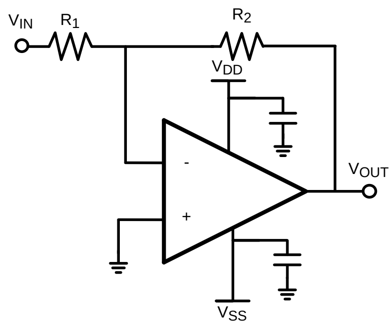


Figure 6. Dual Supply Inverting Op Amp

Figure 7 shows the typical connection for the Buffer Amplifier or also called a Voltage Follower. A Buffer Amplifier can be used to solve impedance matching problems, to reduce power consumption in the source, or to drive heavy loads. The input impedance of the op amp is very high. Therefore, the input of the op amp does not load down the source. The output impedance on the other hand is very low. It allows the load to either supply or absorb energy to a circuit while a secondary voltage source dissipates energy from a circuit. The Buffer is a unity stable amplifier, 1V/V. Although the feedback loop is tied from the output of the amplifier to the inverting input, the gain is still positive. Note, if a positive feedback is used, the amplifier will most likely drive to either rail at the output.

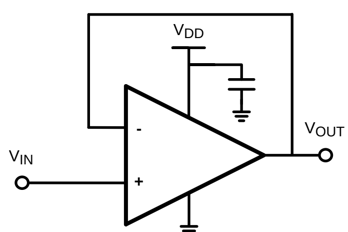


Figure 7. Buffer

Typical Applications

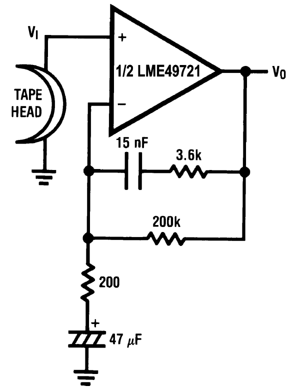


Figure 8. ANAB Preamp

$A_V = 34.5$
F = 1 kHz
$E_n = 0.38$ μV
A Weighted

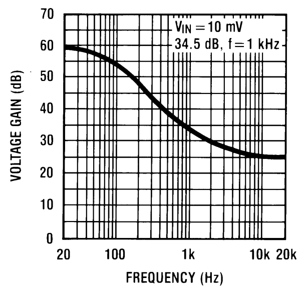


Figure 9. NAB Preamp Voltage Gain vs Frequency

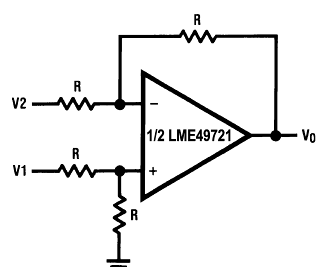


Figure 10. Balanced to Single Ended Converter

$V_O = V1–V2$

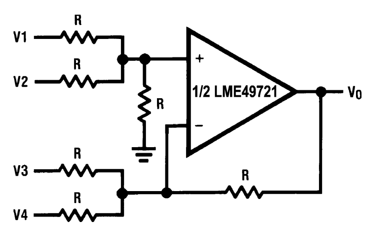
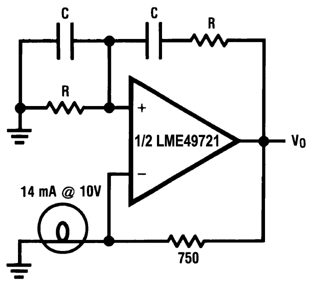


Figure 11. Adder/Subtracter

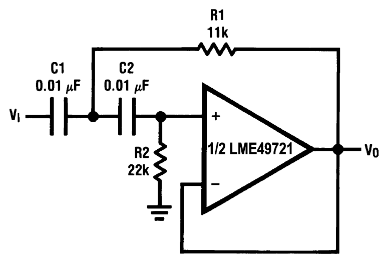
$V_O = V1 + V2 - V3 - V4$

Figure 12. Sine Wave Oscillator



$$f_o = \frac{1}{2\pi RC}$$

Figure 13. Second Order High Pass Filter (Butterworth)



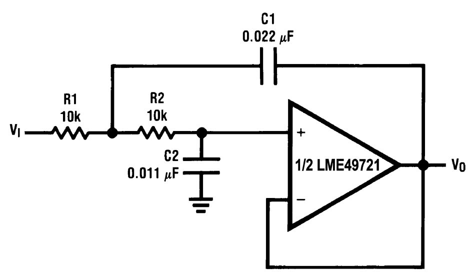
if $C1 = C2 = C$

$$R1 = \frac{\sqrt{2}}{2\omega_o C}$$

$$R2 = 2 \bullet R1$$

Illustration is $f_0 = 1$ kHz

Figure 14. Second Order Low Pass Filter (Butterworth)



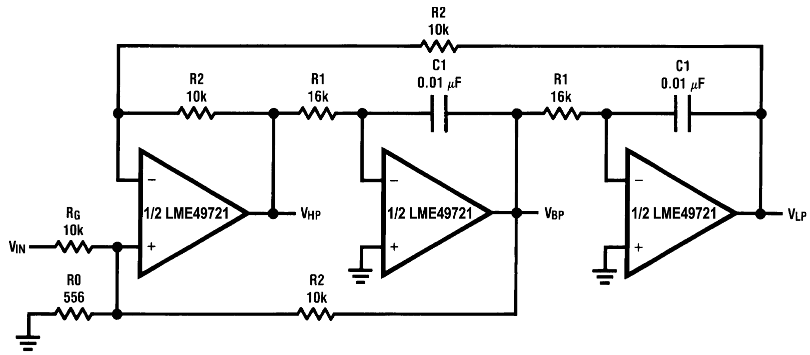
if $R1 = R2 = R$

$$C1 = \frac{\sqrt{2}}{\omega_o R}$$

$$C2 = \frac{C1}{2}$$

Illustration is $f_0 = 1$ kHz

Figure 15. State Variable Filter



$$f_0 = \frac{1}{2\pi C1R1}, Q = \frac{1}{2}\left(1 + \frac{R2}{R0} + \frac{R2}{RG}\right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R2}{RG}$$

Illustration is f_0 = 1 kHz, Q = 10, A_{BP} = 1

Figure 16. AC/DC Converter

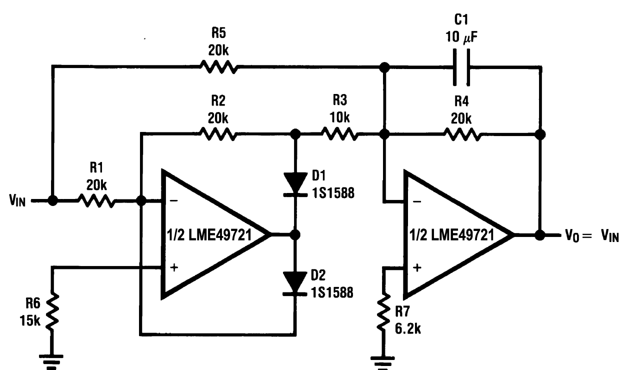


Figure 17. 2 Channel Panning Circuit (Pan Pot)

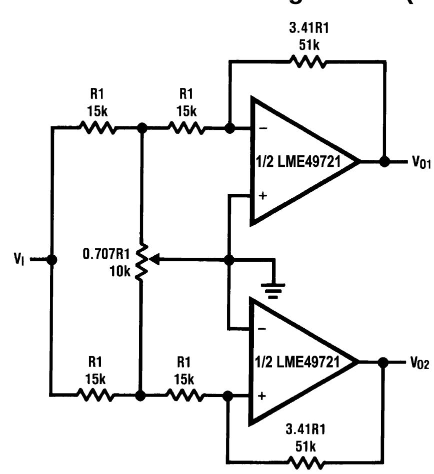


Figure 18. Line Driver

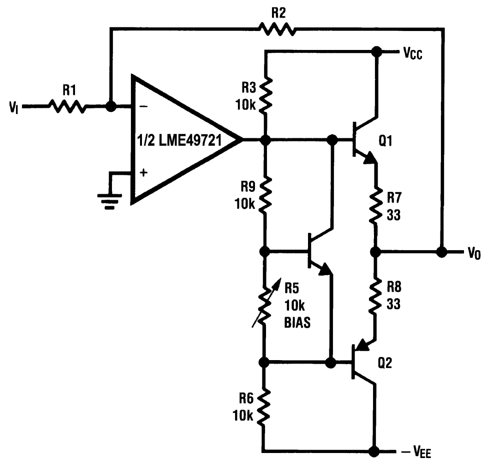
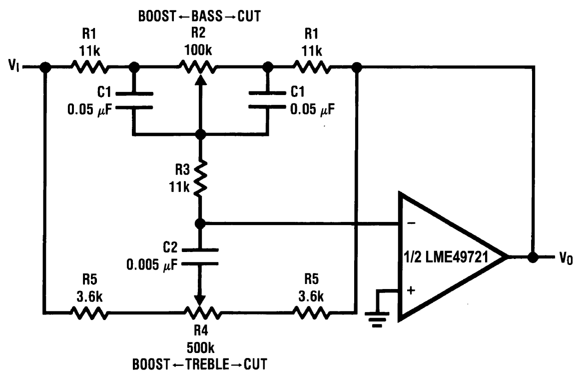


Figure 19. Tone Control



$$f_L = \frac{1}{2\pi R2C1},\ f_{LB} = \frac{1}{2\pi R1C1}$$

$$f_H = \frac{1}{2\pi R5C2},\ f_{HB} = \frac{1}{2\pi (R1 + R5 + 2R3)C2}$$

Illustration is:

f_L = 32 Hz, f_{LB} = 320 Hz

f_H =11 kHz, f_{HB} = 1.1 kHz

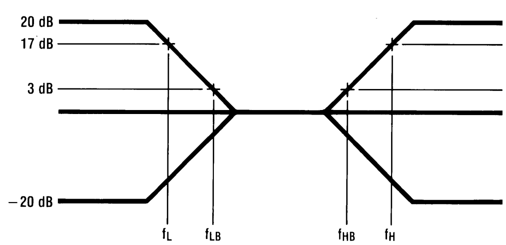
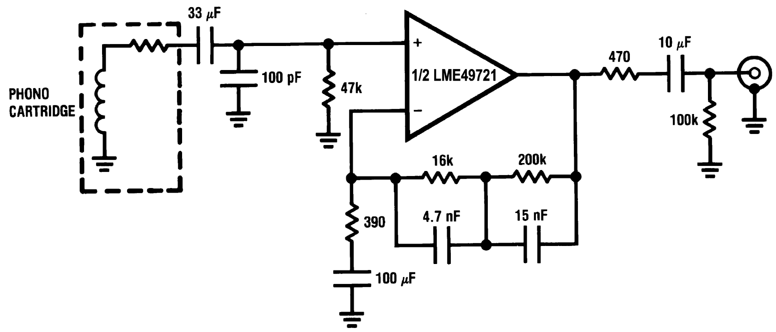
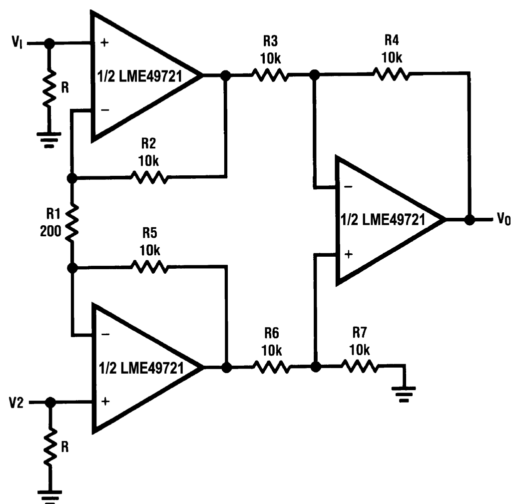


Figure 20. RIAA Preamp



A_v = 35 dB
E_n = 0.33 μV
S/N = 90 dB
f = 1 kHz
A Weighted
A Weighted, V_{IN} = 10 mV
@f = 1 kHz

Figure 21. Balanced Input Mic Amp

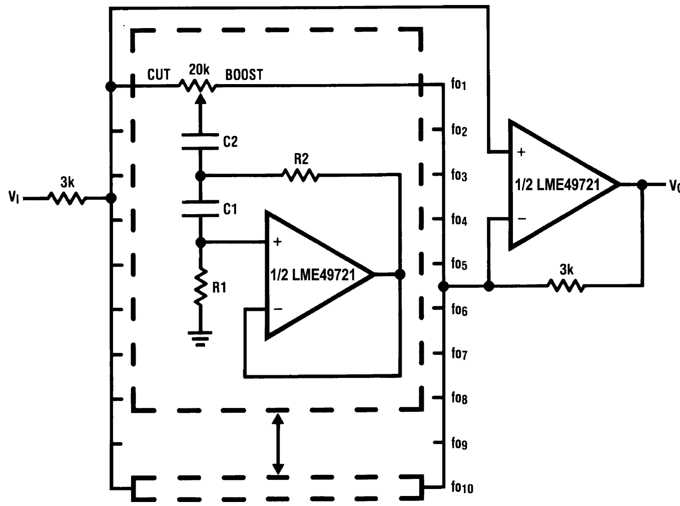


If R2 = R5, R3 = R6, R4 = R7

$$V0 = \left(1 + \frac{2R2}{R1}\right)\frac{R4}{R3}(V2 - V1)$$

Illustration is:
V0 = 101(V2 − V1)

Figure 22. 10 Band Graphic Equalizer



fo (Hz)	C_1	C_2	R_1	R_2
32	0.12μF	4.7μF	75kΩ	500Ω
64	0.056μF	3.3μF	68kΩ	510Ω
125	0.033μF	1.5μF	62kΩ	510Ω
250	0.015μF	0.82μF	68kΩ	470Ω
500	8200pF	0.39μF	62kΩ	470Ω
1k	3900pF	0.22μF	68kΩ	470Ω
2k	2000pF	0.1μF	68kΩ	470Ω
4k	1100pF	0.056μF	62kΩ	470Ω
8k	510pF	0.022μF	68kΩ	510Ω
16k	330pF	0.012μF	51kΩ	510Ω

Revision History

Rev	Date	Description
1.0	09/26/07	Initial release.
1.1	10/01/07	Input more info under the Buffer Amplifier.
1.2	04/21/10	Added the Ordering Information table.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Samples (Requires Login)
LME49721MA/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	
LME49721MAX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

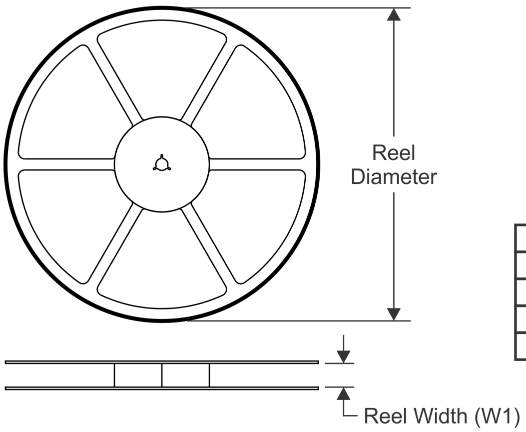
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

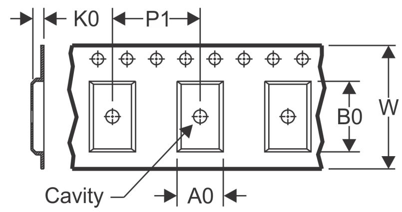
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

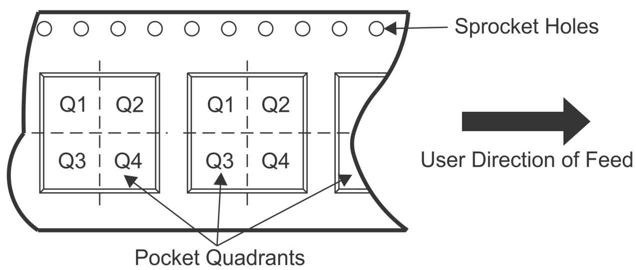


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

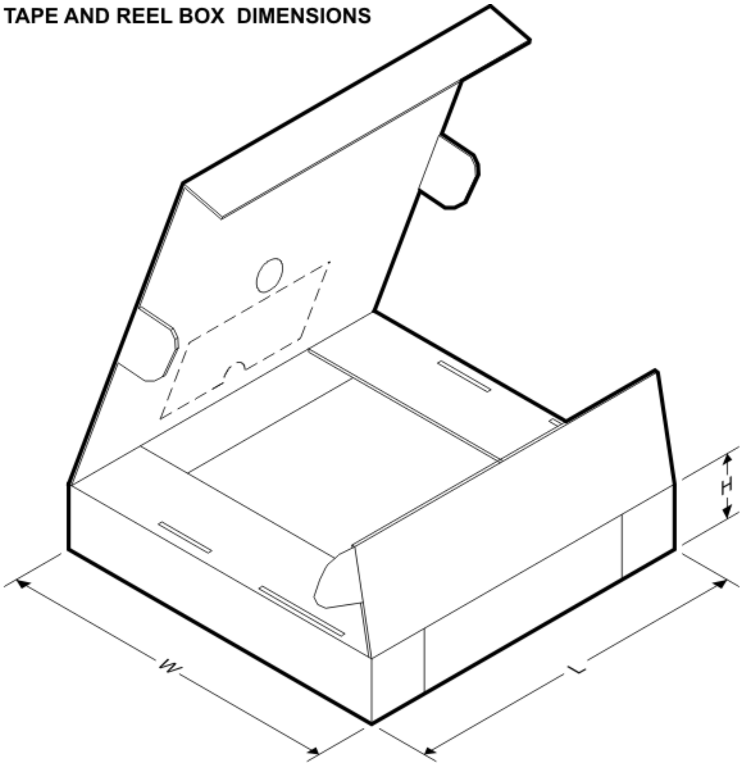
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LME49721MAX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1

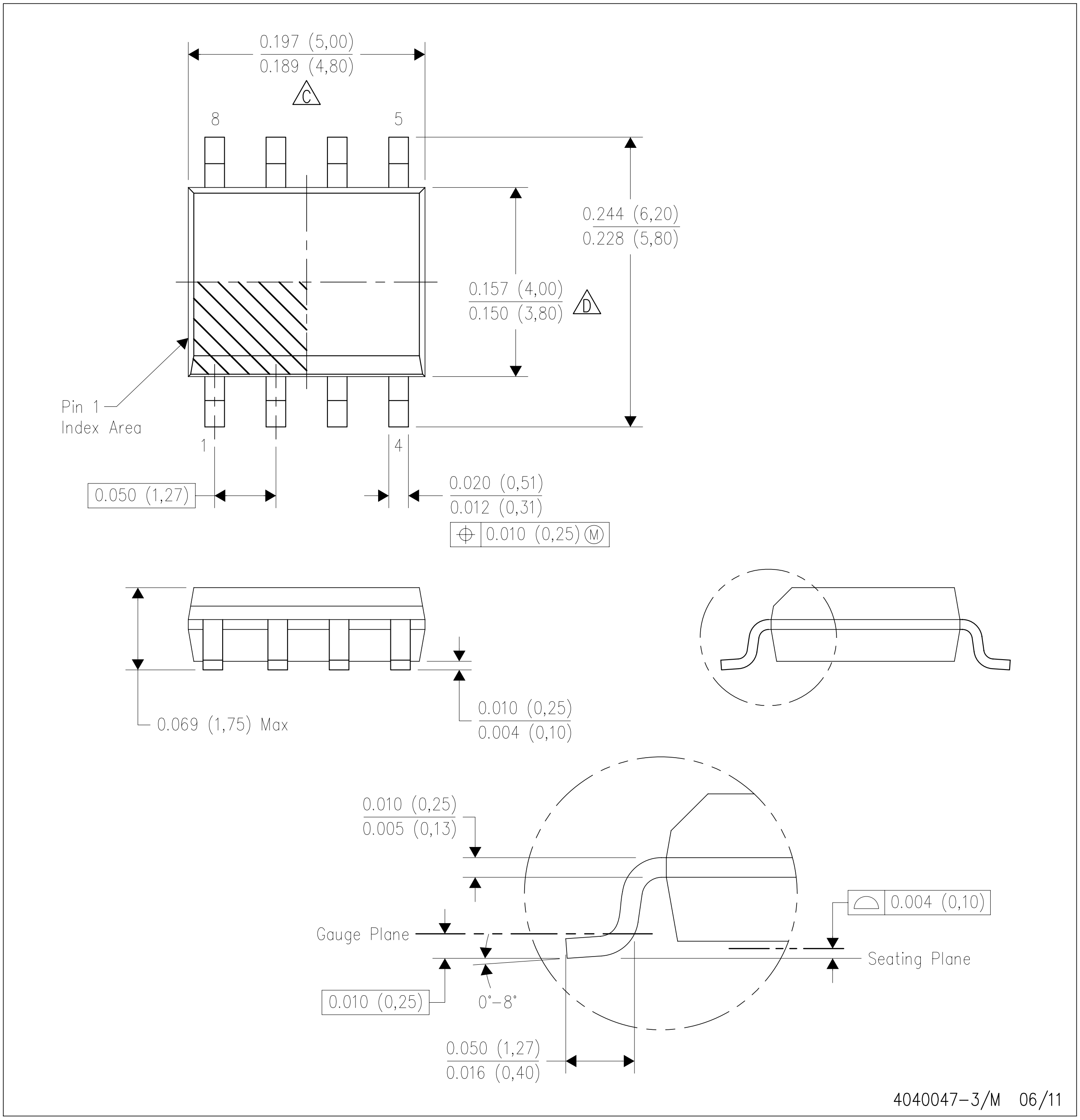
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LME49721MAX/NOPB	SOIC	D	8	2500	349.0	337.0	45.0

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.

IMPORTANT NOTICE

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